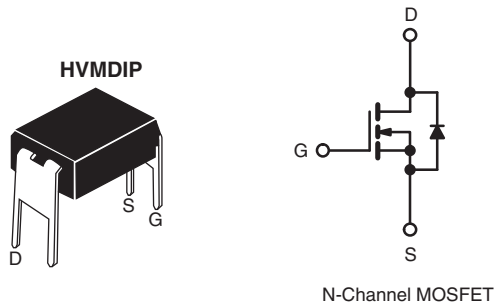


Power MOSFET

PRODUCT SUMMARY	
V_{DS} (V)	200
$R_{DS(on)}$ (Ω)	$V_{GS} = 10\text{ V}$ 1.5
Q_g (Max.) (nC)	8.2
Q_{gs} (nC)	1.8
Q_{gd} (nC)	4.5
Configuration	Single



FEATURES

- Dynamic dV/dt Rating
- Repetitive Avalanche Rated
- For Automatic Insertion
- End Stackable
- Fast Switching
- Ease of Paralleling
- Simple Drive Requirements
- Compliant to RoHS Directive 2002/95/EC



DESCRIPTION

Third generation Power MOSFETs from Vishay provide the designer with the best combination of fast switching, ruggedized device design, low on-resistance and cost-effectiveness.

The 4 pin DIP package is a low cost machine-insertable case style which can be stacked in multiple combinations on standard 0.1" pin centers. The dual drain serves as a thermal link to the mounting surface for power dissipation levels up to 1 W.

ORDERING INFORMATION	
Package	HVMDIP
Lead (Pb)-free	IRFD210PbF SiHFD210-E3
SnPb	IRFD210 SiHFD210

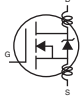

ABSOLUTE MAXIMUM RATINGS ($T_A = 25\text{ }^\circ\text{C}$, unless otherwise noted)				
PARAMETER		SYMBOL	LIMIT	UNIT
Drain-Source Voltage		V_{DS}	200	V
Gate-Source Voltage		V_{GS}	± 20	
Continuous Drain Current	V_{GS} at 10 V	I_D	$T_A = 25\text{ }^\circ\text{C}$	A
			$T_A = 100\text{ }^\circ\text{C}$	
Pulsed Drain Current ^a		I_{DM}	4.8	
Linear Derating Factor			0.0083	W/ $^\circ\text{C}$
Single Pulse Avalanche Energy ^b		E_{AS}	79	mJ
Repetitive Avalanche Current ^a		I_{AR}	0.60	A
Repetitive Avalanche Energy ^a		E_{AR}	0.10	mJ
Maximum Power Dissipation	$T_A = 25\text{ }^\circ\text{C}$	P_D	1.0	W
Peak Diode Recovery dV/dt^c		dV/dt	5.0	V/ns
Operating Junction and Storage Temperature Range		T_J, T_{stg}	- 55 to + 150	$^\circ\text{C}$
Soldering Recommendations (Peak Temperature)	for 10 s		300 ^d	

Notes

- Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11).
- $V_{DD} = 50\text{ V}$, starting $T_J = 25\text{ }^\circ\text{C}$, $L = 82\text{ mH}$, $R_g = 25\text{ }\Omega$, $I_{AS} = 1.2\text{ A}$ (see fig. 12).
- $I_{SD} \leq 3.3\text{ A}$, $dI/dt \leq 70\text{ A}/\mu\text{s}$, $V_{DD} \leq V_{DS}$, $T_J \leq 150\text{ }^\circ\text{C}$.
- 1.6 mm from case.

* Pb containing terminations are not RoHS compliant, exemptions may apply

THERMAL RESISTANCE RATINGS				
PARAMETER	SYMBOL	TYP.	MAX.	UNIT
Maximum Junction-to-Ambient	R_{thJA}	-	120	°C/W

SPECIFICATIONS ($T_J = 25\text{ }^\circ\text{C}$, unless otherwise noted)						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
Static						
Drain-Source Breakdown Voltage	V_{DS}	$V_{GS} = 0\text{ V}$, $I_D = 250\text{ }\mu\text{A}$	200	-	-	V
V_{DS} Temperature Coefficient	$\Delta V_{DS}/T_J$	Reference to $25\text{ }^\circ\text{C}$, $I_D = 1\text{ mA}$	-	0.30	-	V/°C
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = 250\text{ }\mu\text{A}$	2.0	-	4.0	V
Gate-Source Leakage	I_{GSS}	$V_{GS} = \pm 20\text{ V}$	-	-	± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 200\text{ V}$, $V_{GS} = 0\text{ V}$	-	-	25	μA
		$V_{DS} = 160\text{ V}$, $V_{GS} = 0\text{ V}$, $T_J = 125\text{ }^\circ\text{C}$	-	-	250	
Drain-Source On-State Resistance	$R_{DS(on)}$	$V_{GS} = 10\text{ V}$ $I_D = 0.36\text{ A}^b$	-	-	1.5	Ω
Forward Transconductance	g_{fs}	$V_{DS} = 50\text{ V}$, $I_D = 0.36\text{ A}^b$	0.10	-	-	S
Dynamic						
Input Capacitance	C_{iss}	$V_{GS} = 0\text{ V}$ $V_{DS} = 25\text{ V}$ $f = 1.0\text{ MHz}$, see fig. 5	-	140	-	pF
Output Capacitance	C_{oss}		-	53	-	
Reverse Transfer Capacitance	C_{riss}		-	15	-	
Total Gate Charge	Q_g	$V_{GS} = 10\text{ V}$ $I_D = 3.3\text{ A}$, $V_{DS} = 160\text{ V}$ see fig. 6 and 13 ^b	-	-	8.2	nC
Gate-Source Charge	Q_{gs}		-	-	1.8	
Gate-Drain Charge	Q_{gd}		-	-	4.5	
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = 100\text{ V}$, $I_D = 3.3\text{ A}$ $R_g = 24\text{ }\Omega$, $R_D = 30\text{ }\Omega$, see fig. 10 ^b	-	8.2	-	ns
Rise Time	t_r		-	17	-	
Turn-Off Delay Time	$t_{d(off)}$		-	14	-	
Fall Time	t_f		-	8.9	-	
Internal Drain Inductance	L_D	Between lead, 6 mm (0.25") from package and center of die contact 	-	4.0	-	nH
Internal Source Inductance	L_S		-	6.0	-	
Drain-Source Body Diode Characteristics						
Continuous Source-Drain Diode Current	I_S	MOSFET symbol showing the integral reverse p - n junction diode 	-	-	0.60	A
Pulsed Diode Forward Current ^a	I_{SM}		-	-	4.8	
Body Diode Voltage	V_{SD}	$T_J = 25\text{ }^\circ\text{C}$, $I_S = 0.60\text{ A}$, $V_{GS} = 0\text{ V}^b$	-	-	2.0	V
Body Diode Reverse Recovery Time	t_{rr}	$T_J = 25\text{ }^\circ\text{C}$, $I_F = 3.3\text{ A}$, $dI/dt = 100\text{ A}/\mu\text{s}^b$	-	150	310	ns
Body Diode Reverse Recovery Charge	Q_{rr}		-	0.60	1.4	μC
Forward Turn-On Time	t_{on}	Intrinsic turn-on time is negligible (turn-on is dominated by L_S and L_D)				

Notes

- a. Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11)
- b. Pulse width $\leq 300\text{ }\mu\text{s}$; duty cycle $\leq 2\%$

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

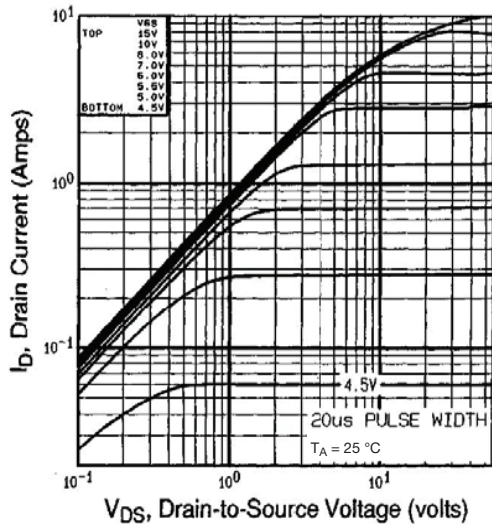


Fig. 1 - Typical Output Characteristics, $T_A = 25\text{ }^\circ\text{C}$

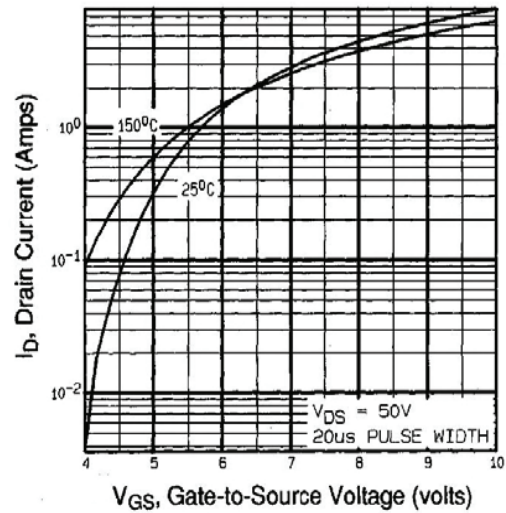


Fig. 3 - Typical Transfer Characteristics

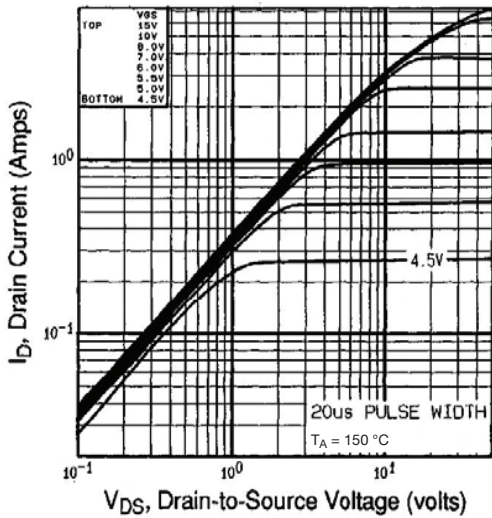


Fig. 2 - Typical Output Characteristics, $T_A = 150\text{ }^\circ\text{C}$

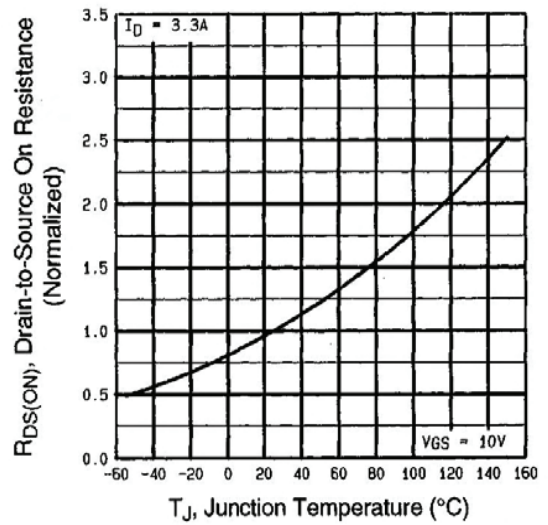


Fig. 4 - Normalized On-Resistance vs. Temperature

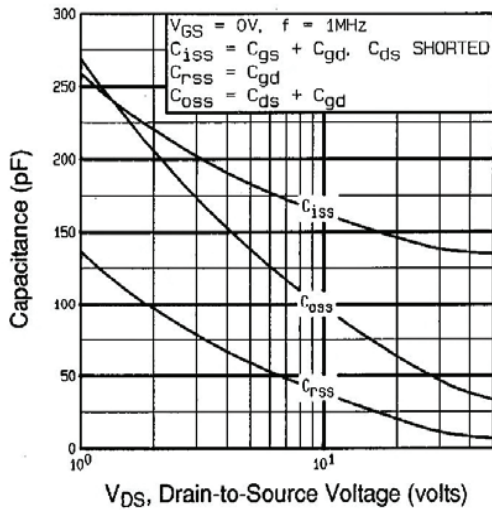


Fig. 5 - Typical Capacitance vs. Drain-to-Source Voltage

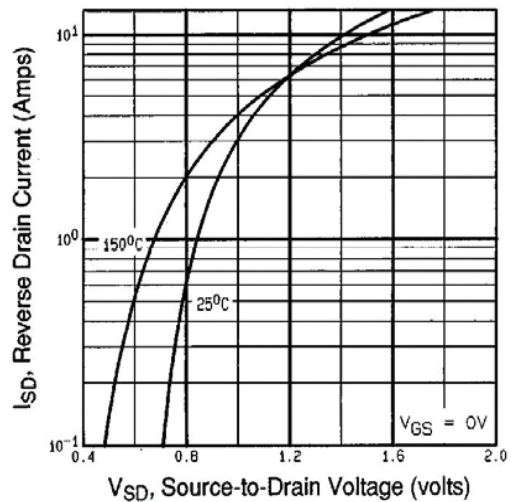


Fig. 7 - Typical Source-Drain Diode Forward Voltage

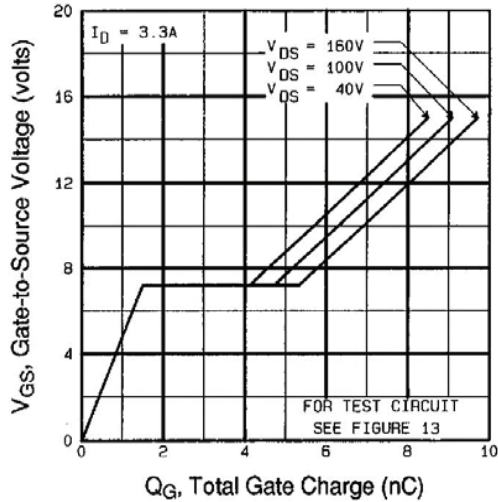


Fig. 6 - Typical Gate Charge vs. Gate-to-Source Voltage

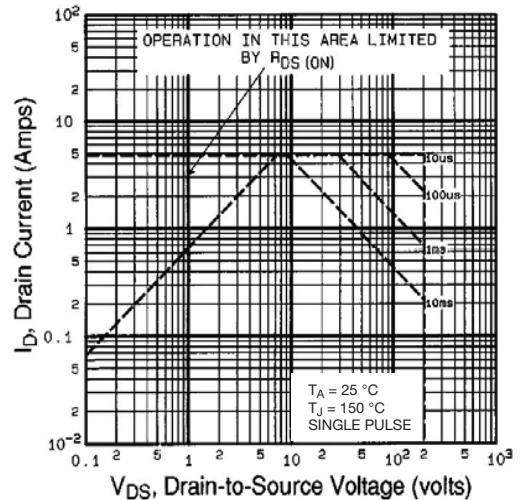


Fig. 8 - Maximum Safe Operating Area

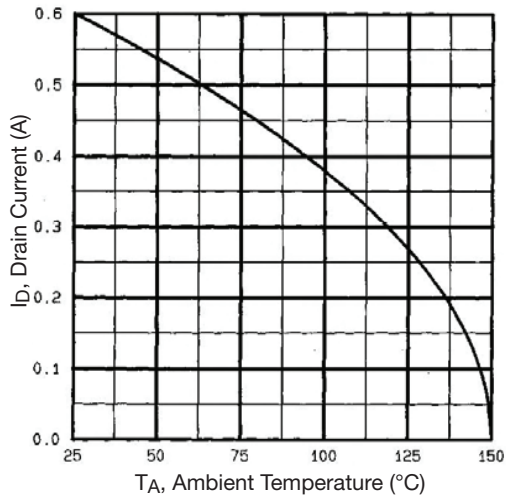


Fig. 9 - Maximum Drain Current vs. Ambient Temperature

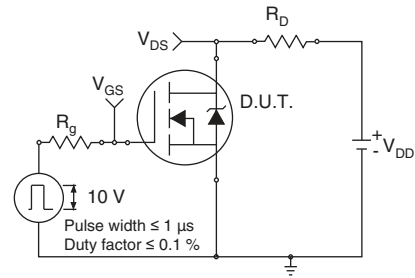


Fig. 10a - Switching Time Test Circuit



Fig. 10b - Switching Time Waveforms

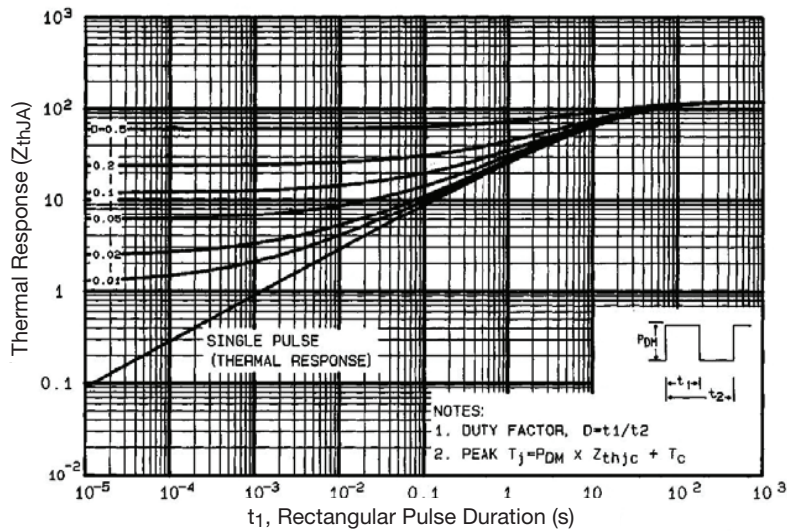


Fig. 11 - Maximum Effective Transient Thermal Impedance, Junction-to-Ambient

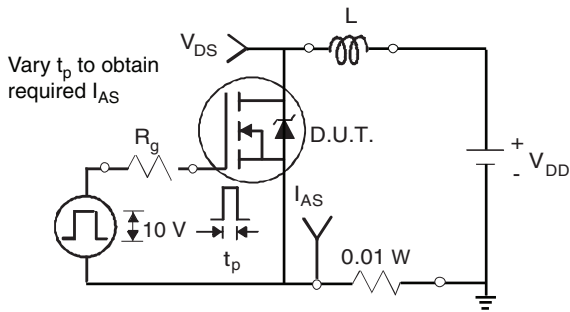


Fig. 12a - Unclamped Inductive Test Circuit



Fig. 12b - Unclamped Inductive Waveforms

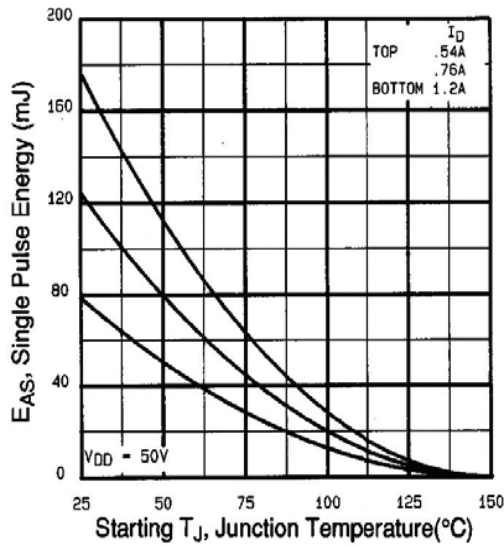


Fig. 12c - Maximum Avalanche Energy vs. Drain Current

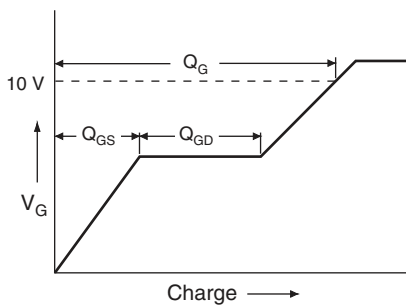


Fig. 13a - Basic Gate Charge Waveform

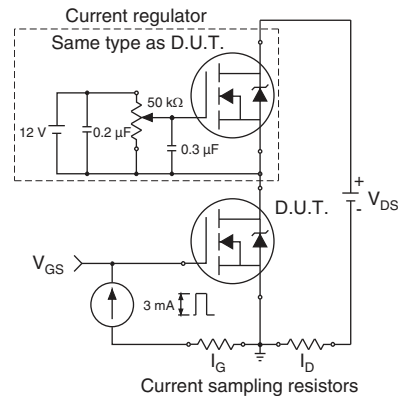


Fig. 13b - Gate Charge Test Circuit



Note

a. $V_{GS} = 5\text{ V}$ for logic level devices

Fig. 14 - For N-Channel

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HVM DIP (High voltage)



DIM.	INCHES		MILLIMETERS	
	MIN.	MAX.	MIN.	MAX.
A	0.310	0.330	7.87	8.38
E	0.300	0.425	7.62	10.79
L	0.270	0.290	6.86	7.36

ECN: X10-0386-Rev. B, 06-Sep-10
DWG: 5974

Note

- Package length does not include mold flash, protrusions or gate burrs. Package width does not include interlead flash or protrusions.



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